

12 June 2003

09/831, 763

L Number	Hits	Search Text	DB	Time stamp
-	1187	205/\$.ccls. and (puls\$3 with current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:51
-	566	(205/\$.ccls. and (puls\$3 with current)) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:50
-	1232	205/\$.ccls. and (puls\$3 with (current or revers\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:51
-	8136	205/\$.ccls. and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	2472	205/\$.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	189	(205/\$.ccls. and (puls\$3 with (current or revers\$3))) and (205/\$.ccls. and copper) and (205/\$.ccls. and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	150	((205/\$.ccls. and (puls\$3 with (current or revers\$3))) and (205/\$.ccls. and copper) and (205/\$.ccls. and semiconductor)) and (recess or trench or via or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 15:01
-	22	(((205/\$.ccls. and (puls\$3 with (current or revers\$3))) and (205/\$.ccls. and copper) and (205/\$.ccls. and semiconductor)) and (recess or trench or via or hole)) and ((inert or noble or titanium) near (anode or electrode or counterelectrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
-	2	"6432293"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 15:24
-	1	2000-642506.NRAN.	DERWENT	2003/06/11 15:22
-	61	205/\$.ccls. and damascen and puls\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:06

	258	205/\$.ccls. and ((cathodic or plating or forward) adj (current or pulse)) and ((anodic or polishing or etching or dissolution) adj (current or pulse))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:09
	43	(205/\$.ccls. and ((cathodic or plating or forward) adj (current or pulse)) and ((anodic or polishing or etching or dissolution) adj (current or pulse))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:09
	2	gb-2214520-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 08:47
	35091	205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:03
	2587	205/\$.ccls. and (semiconductor or (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:19
	1589	(205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
	918	((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
	286	((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
	48	(((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
	336	(205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31

	63	((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
	15	(((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))) not (((205/\$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat\$4 or electrochem\$6 or electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
	782	205/291-298.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
	118	205/291-298.ccls. and (iron or fe! or ferrous or ferric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
	106	205/291-298.ccls. and (semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:35
	28	(205/291-298.ccls. and (iron or fe! or ferrous or ferric)) and (205/291-298.ccls. and (semiconductor or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:37
	2	6099711.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:38
	9	"6099711"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:38
	1	1997-282330.NRAN.	DERWENT	2003/06/12 09:38
	3205	205/101,102,103,104,118,122,123,157,183,220,221,291,292	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:50

	505	205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole)	29125PAt;	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
	549	205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)	29125PAt;	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
	391	(205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper	29125PAt;	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
	220	((205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)	29125PAt.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:52
	69	(((205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls\$3	29125PAt.s.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:52
	69	(((205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls\$5	29125PAt.s.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 12:06
	44	(((205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls\$5) and ((semiconductor or silicon) with (circuit))	29125PAtcls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 12:09
	9	(((205/101,102,103,104,118,122,123,157,183,220,221,291, and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls\$5) and ((semiconductor or silicon) with (circuit adj board))	29125PAtcls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:18
	1	de-4344387-a1.did.	USPAT;	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:22
	1	1995-232640.NRAN.	USPAT;	US-PGPUB; EPO; JPO; DERWENT;	2003/06/12 14:20
	9	"5976341"	USPAT;	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:22